Silicon NPN Power Transistors 2SC2358

DESCRIPTION

·With TO-3 package
·High voltage,high speed

APPLICATIONS

·Designed for switching-mode power supplies ,CRT scanning,inverters, and other industrial applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

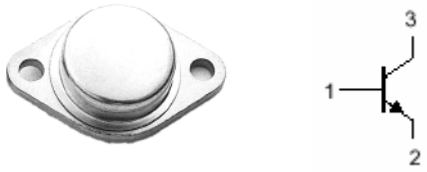

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
P_T	Total power dissipation	T_C=25□	150	W
T_j	Junction temperature		200	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	1.17	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=10mA; I_B=0	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1m A;I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5 A;I_B=1 A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5 A;I_B=1 A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=1000V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=5V	15			

PACKAGE OUTLINE

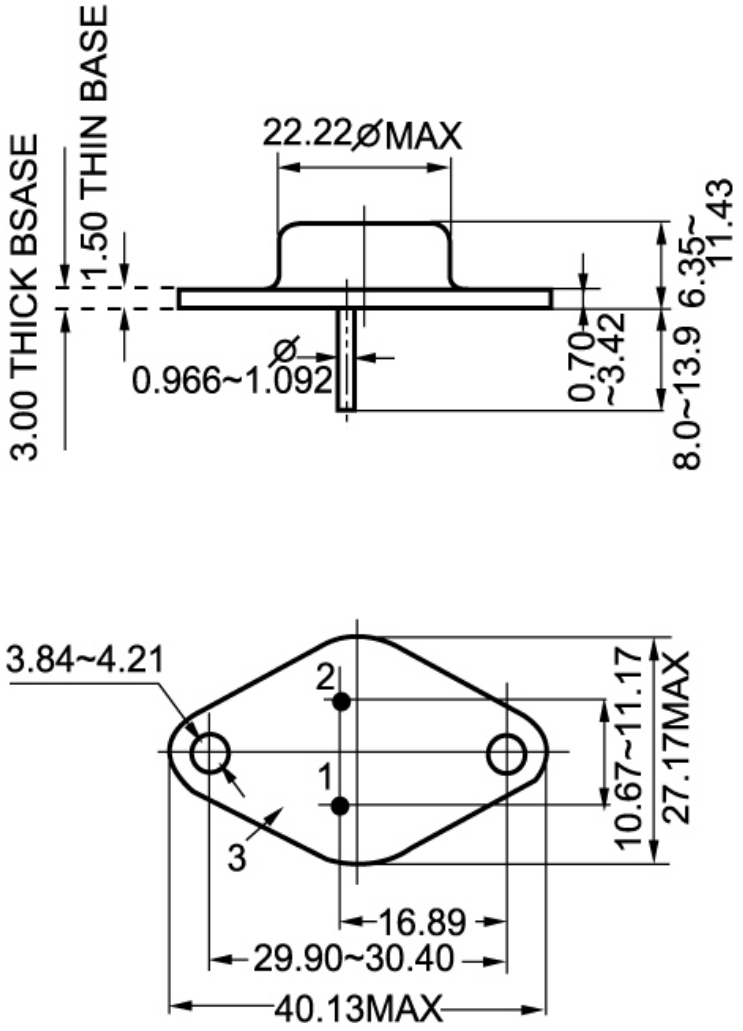

Fig.2 Outline dimensions